

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device having a portion thereof formed from a wafer of semiconductive material by a laser etching process comprising:
a substrate of semiconductive wafer material having a surface ~~having a roughened surface thereon formed by a laser;~~
an interposer connected to the substrate, the interposer having a roughened surface formed by a laser increasing the surface area thereof to adhere mold material thereto in a molding operation;
and
resist on at least a portion of the surface of the substrate of semiconductive wafer material having a portion thereof removed by etching the resist from the surface of the substrate using a laser.

2. (Previously Presented) The semiconductor device according to claim 1, wherein the laser comprises a laser associated with an automolding system.

3. (Previously Presented) The semiconductor device according to claim 1, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

4. (Previously Presented) The semiconductor device according to claim 1, wherein the substrate comprises a ball-grid-array substrate.

5. (Previously Presented) The semiconductor device according to claim 1, further comprising a vision system for detecting the resist.

6. (Previously Presented) The semiconductor device according to claim 5, wherein the vision system comprises:
a laser scanning system for detecting changes in a pattern of the substrate.

7 - 11 (Canceled)

12. (Currently Amended) A semiconductor device having a portion formed by a laser etching process on a substrate of semiconductive material having a surface comprising: resist located on at least a portion of the surface having a portion thereof removed by etching the resist from the at least a portion of the surface of the substrate using a laser forming a roughened surface on the surface of the substrate of semiconductive material increasing the surface area of the surface to adhere mold material thereto.

13. (Previously Presented) The semiconductor device according to claim 12, wherein the laser comprises a laser associated with an automolding system.

14. (Previously Presented) The semiconductor device according to claim 12, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

15. (Previously Presented) The semiconductor device according to claim 12, wherein the substrate comprises a ball-grid-array substrate.

16. (Previously Presented) The semiconductor device according to claim 12, further comprising a vision system for detecting the resist.

17. (Previously Presented) The semiconductor device according to claim 16, wherein the vision system comprises: a laser scanning system for detecting changes in a pattern of the substrate.